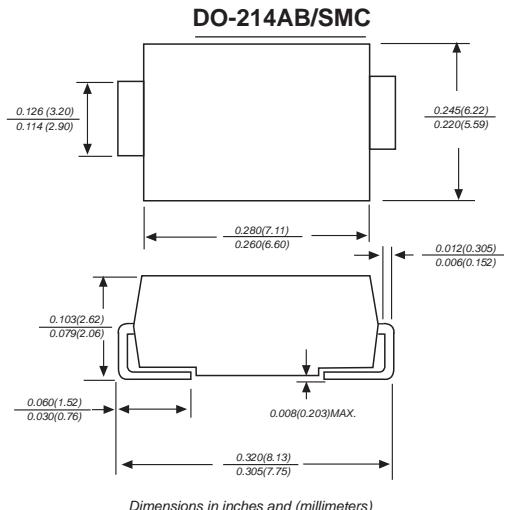




# ES5A THRU ES5J

## SURFACE MOUNT SUPER FAST RECTIFIER

Reverse Voltage - 50 to 600 Volts Forward Current - 5.0 Amperes



Dimensions in inches and (millimeters)

### FEATURES

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- For surface mounted applications
- Low reverse leakage
- Built-in strain relief, ideal for automated placement
- High forward surge current capability
- High temperature soldering guaranteed: 250°C/10 seconds at terminals
- Glass passivated chip junction

### MECHANICAL DATA

**Case :** JEDEC DO-214AB molded plastic body over passivated chip

**Terminals :** Solder plated, solderable per MIL-STD-750,

Method 2026

**Polarity :** Color band denotes cathode end

**Mounting Position :** Any

**Weight :** 0.007 ounce, 0.25grams

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

MDD Catalog Number	SYMBOLS	ES5A	ES5B	ES5C	ES5D	ES5E	ES5G	ES5J	UNITS
Marking code		MDD ES5A	MDD ES5B	MDD ES5C	MDD ES5D	MDD ES5E	MDD ES5G	MDD ES5J	
Maximum repetitive peak reverse voltage	V <sub>RRM</sub>	50	100	150	200	300	400	600	VOLTS
Maximum RMS voltage	V <sub>RMS</sub>	35	70	105	140	210	280	420	VOLTS
Maximum DC blocking voltage	V <sub>DC</sub>	50	100	150	200	300	400	600	VOLTS
Maximum average forward rectified current at T <sub>L</sub> =75°C	I <sub>(AV)</sub>								Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>			150			135		Amps
Maximum instantaneous forward voltage at 5.0A	V <sub>F</sub>		1.0		1.25	1.7			Volts
Maximum DC reverse current TA=25°C at rated DC blocking voltage TA=100°C	I <sub>R</sub>			10.0	100.0				µA
Maximum reverse recovery time (NOTE 1)	t <sub>rr</sub>			35					ns
Typical junction capacitance (NOTE 2)	C <sub>J</sub>			95.0					pF
Typical thermal resistance (NOTE 3)	R <sub>θJA</sub>			45.0					°C/W
Operating junction and storage temperature range	T <sub>J,TSTG</sub>			-50 to +150					°C

**Note:** 1. Reverse recovery condition I<sub>F</sub>=0.5A, I<sub>R</sub>=1.0A, I<sub>rr</sub>=0.25A

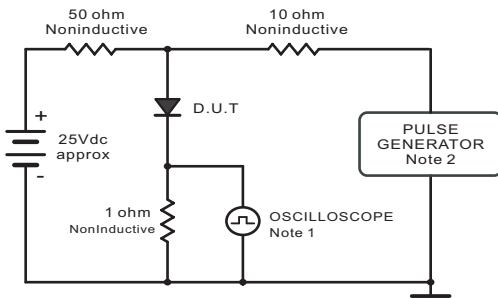
2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

3. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas

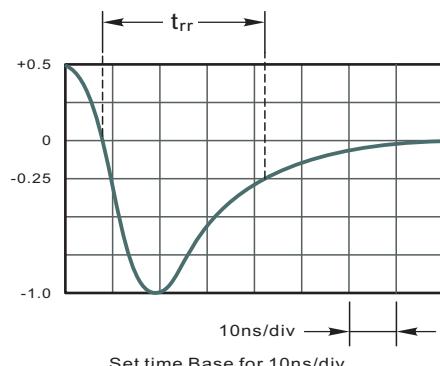


# RATINGS AND CHARACTERISTIC CURVES ES5A THRU ES5J

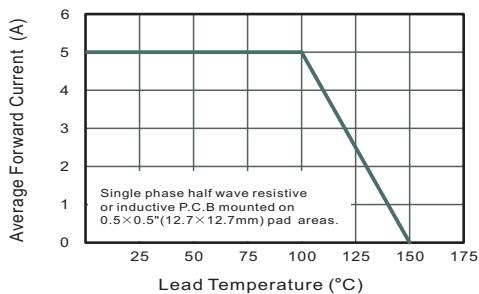
**Fig.1 Reverse Recovery Time Characteristic And Test Circuit Diagram**



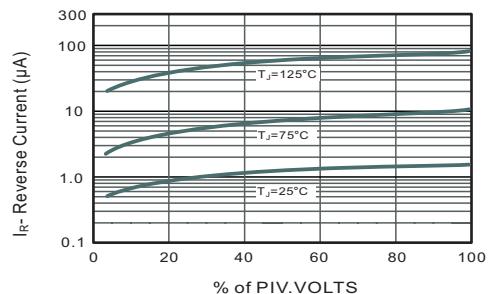
Note: 1. Rise Time = 7ns, max.  
Input Impedance = 1megohm, 22pF.  
2. Ries Time = 10ns, max.  
Source Impedance = 50 ohms.



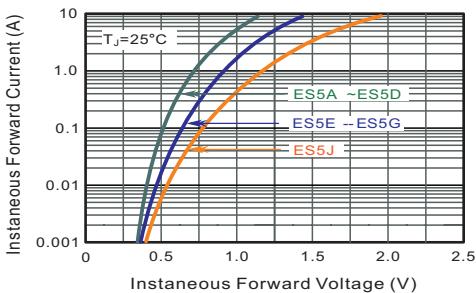
**Fig.2 Maximum Average Forward Current Rating**



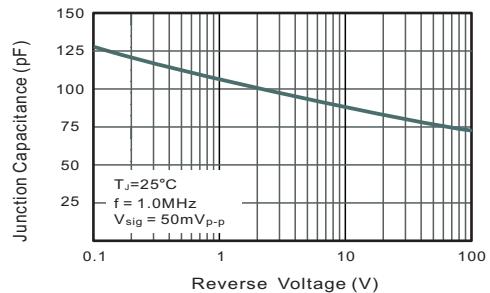
**Fig.3 Typical Reverse Characteristics**



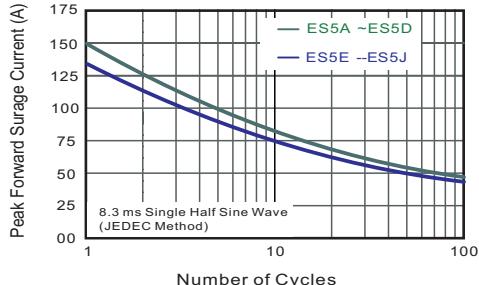
**Fig.4 Typical Forward Characteristics**



**Fig.5 Typical Junction Capacitance**



**Fig.6 Maximum Non-Repetitive Peak Forward Surge Current**



The curve graph is for reference only, can't be the basis for judgment(曲线图仅供参考)!

